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December 2013

### FQP3N60C

## N-Channel QFET® MOSFET

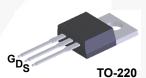
600 V, 3.0 A, 3.4  $\Omega$ 

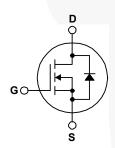
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 3.0 A, 600 V,  $R_{DS(on)}$  = 3.4  $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 1.5 A
- Low Gate Charge (Typ. 10.5 nC)
- Low Crss (Typ. 5.0 pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol Parameter		FQP3N60C	Unit		
V <sub>DSS</sub>	Drain-Source Voltage		600	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)		3 1.8	A A	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	12	Α	
V <sub>GSS</sub>	Gate-Source voltage		±30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy		150	mJ	
I <sub>AR</sub>	Avalanche Current		3	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy		7.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C		75 0.62	W W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FQP3N60C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.67	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	* C/VV

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP3N60C	FQP3N60C	TO-220	Tube	N/A	N/A	50 units

### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics			ı		I
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.6		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125°C			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A		2.8	3.4	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 1.5 A		3.5		S
Dynamic C	Characteristics			•		
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		435	565	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		45	60	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			5	8	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 3 A		12	34	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		30	70	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			35	80	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	35	80	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 480 V, I <sub>D</sub> = 3 A		10.5	14	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		2.1		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		4.5		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				3	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				12	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3 A		260	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 \text{ A}/\mu\text{s}$	/	1.6	/	μС

#### Notes:

 $<sup>{\</sup>bf 1.}\ Repetitive\ rating: pulse-width\ limited\ by\ maximum\ junction\ temperature.$ 

<sup>2.</sup> L= 30 mH, I $_{AS}$  = 3 A, V $_{DD}$  = 50 V, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C.

 $<sup>3.</sup>I_{SD} \leq 3 \text{ A, di/dt} \leq 200 \text{ A/}\mu\text{s, V}_{DD} \leq \text{BV}_{DSS_i} \text{ Starting } \text{ T}_J \text{ = } 25^{\circ}\text{C}.$ 

 $<sup>{\</sup>bf 4.} \ {\bf Essentially \ independent \ of \ operating \ temperature}.$ 

### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

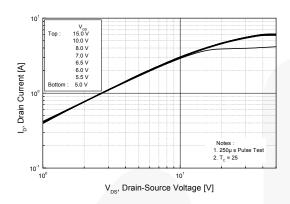


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

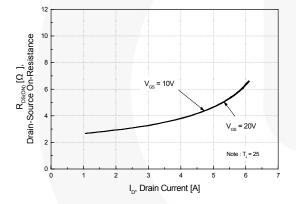


Figure 5. Capacitance Characteristics

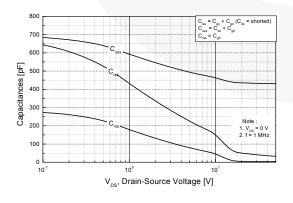


Figure 2. Transfer Characteristics

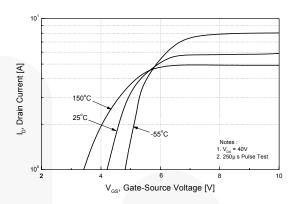


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

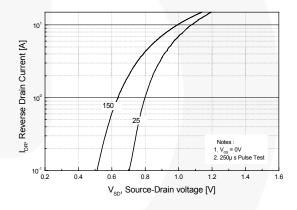
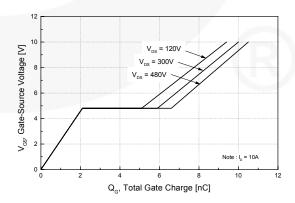


Figure 6. Gate Charge Characteristics



### **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

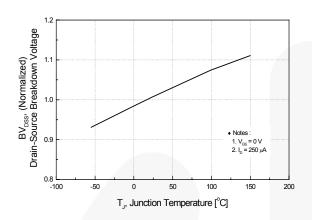


Figure 8. On-Resistance Variation vs. Temperature

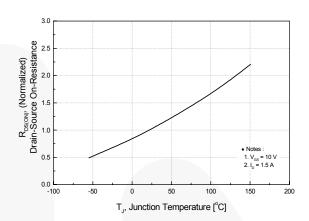


Figure 9. Maximum Safe Operating Area

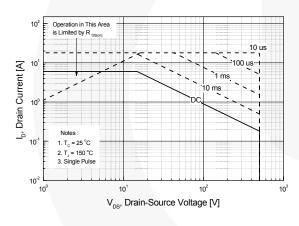


Figure 10. Maximum Drain Current vs. Case Temperature

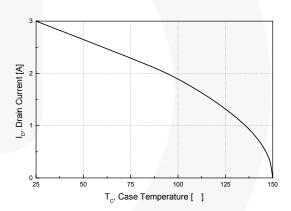
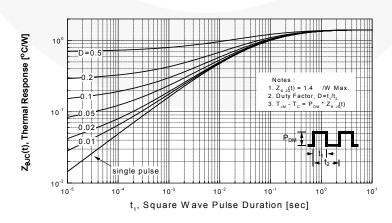


Figure 11. Transient Thermal Response Curve



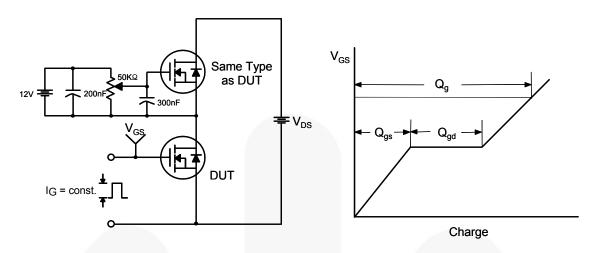


Figure 12. Gate Charge Test Circuit & Waveform

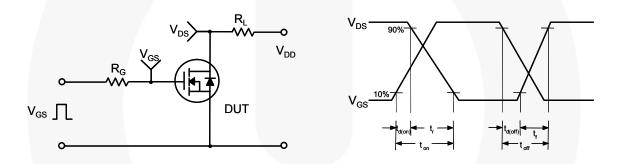


Figure 13. Resistive Switching Test Circuit & Waveforms

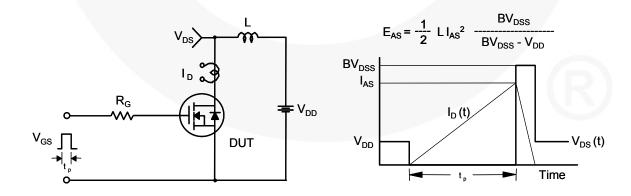


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

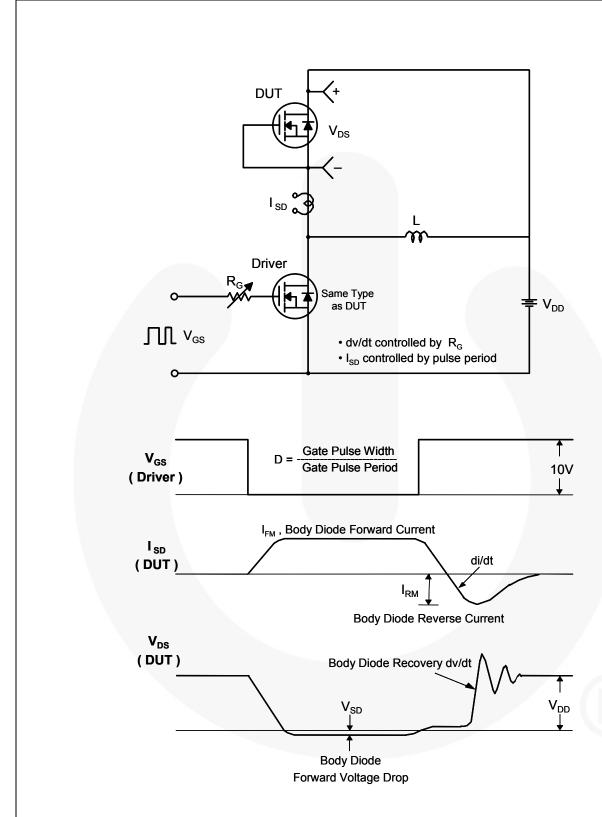


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

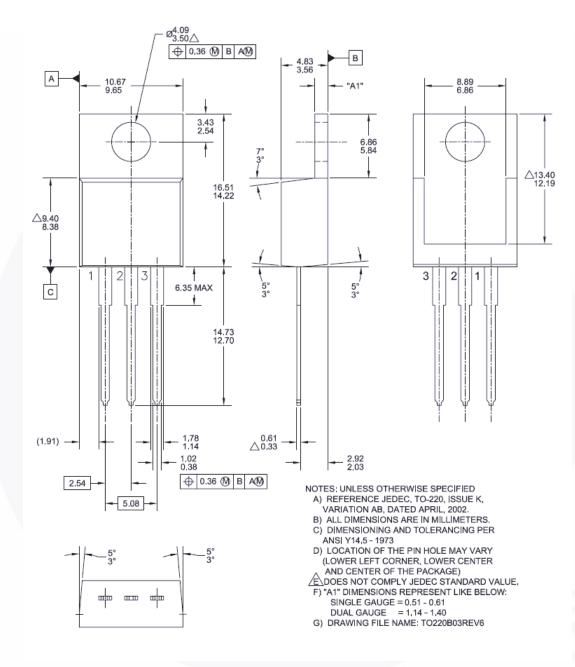


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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